

# Michael Kneissl

## List of Publications by Citations

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351  
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8,555  
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43  
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78  
g-index

394  
ext. papers

9,743  
ext. citations

2.7  
avg, IF

5.99  
L-index

#	Paper	IF	Citations
351	Advances in group III-nitride-based deep UV light-emitting diode technology. <i>Semiconductor Science and Technology</i> , <b>2011</b> , 26, 014036	1.8	525
350	The emergence and prospects of deep-ultraviolet light-emitting diode technologies. <i>Nature Photonics</i> , <b>2019</b> , 13, 233-244	33.9	458
349	Fabrication of thin-film InGaN light-emitting diode membranes by laser lift-off. <i>Applied Physics Letters</i> , <b>1999</b> , 75, 1360-1362	3.4	284
348	Application of GaN-based ultraviolet-C light emitting diodes--UV LEDs--for water disinfection. <i>Water Research</i> , <b>2011</b> , 45, 1481-9	12.5	281
347	Unidirectional lasing from InGaN multiple-quantum-well spiral-shaped micropillars. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 1710-1712	3.4	230
346	InxGa1-xN light emitting diodes on Si substrates fabricated by PdIn metal bonding and laser lift-off. <i>Applied Physics Letters</i> , <b>2000</b> , 77, 2822-2824	3.4	159
345	Metastability of Oxygen Donors in AlGaIn. <i>Physical Review Letters</i> , <b>1998</b> , 80, 4008-4011	7.4	138
344	AlGaIn-based deep UV LEDs grown on sputtered and high temperature annealed AlN/sapphire. <i>Applied Physics Letters</i> , <b>2018</b> , 112, 041110	3.4	136
343	Optical polarization characteristics of ultraviolet (In)(Al)GaIn multiple quantum well light emitting diodes. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 171105	3.4	127
342	Ultraviolet semiconductor laser diodes on bulk AlN. <i>Journal of Applied Physics</i> , <b>2007</b> , 101, 123103	2.5	126
341	Effect of strain and barrier composition on the polarization of light emission from AlGaIn/AlN quantum wells. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 021101	3.4	124
340	The 2020 UV emitter roadmap. <i>Journal Physics D: Applied Physics</i> , <b>2020</b> , 53, 503001	3	123
339	Current-injection spiral-shaped microcavity disk laser diodes with unidirectional emission. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 2485-2487	3.4	115
338	Indium incorporation and emission wavelength of polar, nonpolar and semipolar InGaIn quantum wells. <i>Semiconductor Science and Technology</i> , <b>2012</b> , 27, 024014	1.8	113
337	Quantitative analysis of the polarization fields and absorption changes in InGaIn/GaN quantum wells with electroabsorption spectroscopy. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 490-492	3.4	102
336	Nitride emitters go nonpolar. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2007</b> , 1, A44-A46	2.5	95
335	Performance Characteristics of UV-C AlGaIn-Based Lasers Grown on Sapphire and Bulk AlN Substrates. <i>IEEE Photonics Technology Letters</i> , <b>2014</b> , 26, 342-345	2.2	92

334	The critical thickness of InGaN on (0001)GaN. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 4913-4915	1.6	87
333	Efficient charge carrier injection into sub-250 nm AlGaIn multiple quantum well light emitting diodes. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 051113	3.4	83
332	High quality AlGaIn grown on ELO AlN/sapphire templates. <i>Journal of Crystal Growth</i> , <b>2013</b> , 377, 32-36	1.6	83
331	Characterization of AlGaInN diode lasers with mirrors from chemically assisted ion beam etching. <i>Applied Physics Letters</i> , <b>1998</b> , 72, 1539-1541	3.4	76
330	Near-bandedge cathodoluminescence of an AlN homoepitaxial film. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 3501-3503	3.4	75
329	Highly conductive n-Al <sub>x</sub> Ga <sub>1-x</sub> N layers with aluminum mole fractions above 80%. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 212109	3.4	72
328	Low-threshold stimulated emission at 249 nm and 256 nm from AlGaIn-based multiple-quantum-well lasers grown on sapphire substrates. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 141106	3.4	68
327	Effect of the AlN nucleation layer growth on AlN material quality. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 4932-4934	1.6	68
326	High gain ultraviolet photodetectors based on AlGaIn/GaN heterostructures for optical switching. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 211114	3.4	66
325	Ultraviolet AlGaIn multiple-quantum-well laser diodes. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 4441-4443	3.4	66
324	Determination of the piezoelectric field in InGaIn quantum wells. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 131108	3.4	66
323	Influence of microstructure on the carrier concentration of Mg-doped GaN films. <i>Applied Physics Letters</i> , <b>2001</b> , 79, 2734-2736	3.4	66
322	Strongly transverse-electric-polarized emission from deep ultraviolet AlGaIn quantum well light emitting diodes. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 142101	3.4	63
321	Optically pumped UV lasers grown on bulk AlN substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2012</b> , 9, 822-825		62
320	Continuous-wave operation of ultraviolet InGaIn/InAlGaIn multiple-quantum-well laser diodes. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 2386-2388	3.4	59
319	Polycrystalline nitride semiconductor light-emitting diodes fabricated on quartz substrates. <i>Applied Physics Letters</i> , <b>2000</b> , 76, 2182-2184	3.4	58
318	Structural and optical properties of nonpolar GaN thin films. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 171904	3.4	56
317	Enhancement of light extraction in ultraviolet light-emitting diodes using nanopixel contact design with Al reflector. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 081109	3.4	54

316	Growth of AlGa <sub>N</sub> and AlN on patterned AlN/sapphire templates. <i>Journal of Crystal Growth</i> , <b>2011</b> , 315, 200-203	1.6	54
315	Continuous-wave InGa <sub>N</sub> multiple-quantum-well laser diodes on copper substrates. <i>Applied Physics Letters</i> , <b>2001</b> , 78, 1198-1200	3.4	54
314	Effective Thermal Management in Ultraviolet Light-Emitting Diodes With Micro-LED Arrays. <i>IEEE Transactions on Electron Devices</i> , <b>2013</b> , 60, 782-786	2.9	53
313	Laser gain properties of AlGa <sub>N</sub> quantum wells. <i>Journal of Applied Physics</i> , <b>2005</b> , 98, 114502	2.5	52
312	Vertical injection thin-film AlGa <sub>N</sub> /AlGa <sub>N</sub> multiple-quantum-well deep ultraviolet light-emitting diodes. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 241113	3.4	52
311	Room-temperature continuous-wave operation of InGa <sub>N</sub> multiple-quantum-well laser diodes with an asymmetric waveguide structure. <i>Applied Physics Letters</i> , <b>1999</b> , 75, 581-583	3.4	47
310	A Brief Review of III-Nitride UV Emitter Technologies and Their Applications. <i>Springer Series in Materials Science</i> , <b>2016</b> , 1-25	0.9	46
309	. <i>IEEE Photonics Technology Letters</i> , <b>2012</b> , 24, 1603-1605	2.2	43
308	Effect of the barrier composition on the polarization fields in near UV InGa <sub>N</sub> light emitting diodes. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 191912	3.4	43
307	High-temperature growth of AlN in a production scale 11 $\Omega$ ? MOVPE reactor. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2008</b> , 5, 1799-1801		43
306	Integration of GaN thin films with dissimilar substrate materials by Pd-In metal bonding and laser lift-off. <i>Journal of Electronic Materials</i> , <b>1999</b> , 28, 1409-1413	1.9	43
305	. <i>IEEE Transactions on Electron Devices</i> , <b>2017</b> , 64, 200-205	2.9	41
304	Auger recombination in AlGa <sub>N</sub> quantum wells for UV light-emitting diodes. <i>Applied Physics Letters</i> , <b>2018</b> , 113, 071107	3.4	41
303	Impact of band structure and transition matrix elements on polarization properties of the photoluminescence of semipolar and nonpolar InGa <sub>N</sub> quantum wells. <i>Physica Status Solidi (B): Basic Research</i> , <b>2011</b> , 248, 638-646	1.3	41
302	Semipolar GaN grown on m-plane sapphire using MOVPE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2008</b> , 5, 1815-1817		41
301	Ultraviolet InAlGa <sub>N</sub> Light Emitting Diodes Grown on Hydride Vapor Phase Epitaxy AlGa <sub>N</sub> /Sapphire Templates. <i>Japanese Journal of Applied Physics</i> , <b>2006</b> , 45, 3905-3908	1.4	40
300	Surface diffusion and layer morphology of ((112 $\bar{1}$ 2)) GaN grown by metal-organic vapor phase epitaxy. <i>Journal of Applied Physics</i> , <b>2012</b> , 111, 033526	2.5	39
299	Low absorption loss p-AlGa <sub>N</sub> superlattice cladding layer for current-injection deep ultraviolet laser diodes. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 151108	3.4	39

298	High-power UV-B LEDs with long lifetime <b>2015</b> ,		38
297	Improved injection efficiency in 290 nm light emitting diodes with Al(Ga)N electron blocking heterostructure. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 031109	3-4	38
296	MOVPE growth of semipolar AlN on m-plane sapphire. <i>Journal of Crystal Growth</i> , <b>2012</b> , 355, 59-62	1.6	37
295	Electrical properties and microstructure of vanadium-based contacts on ICP plasma etched n-type AlGa <sub>x</sub> N:Si and GaN:Si surfaces. <i>Semiconductor Science and Technology</i> , <b>2013</b> , 28, 125015	1.8	37
294	Orientation control of GaN {112̄0} and {101̄10} grown on (101̄0) sapphire by metal-organic vapor phase epitaxy. <i>Journal of Crystal Growth</i> , <b>2010</b> , 312, 2171-2174	1.6	37
293	Room-temperature pulsed operation of an electrically injected InGa <sub>x</sub> N/GaN multi-quantum well distributed feedback laser. <i>Applied Physics Letters</i> , <b>1998</b> , 73, 2158-2160	3-4	37
292	Phase separation in InGa <sub>x</sub> N multiple quantum wells annealed at high nitrogen pressures. <i>Applied Physics Letters</i> , <b>1999</b> , 75, 3950-3952	3-4	36
291	Degradation effects of the active region in UV-C light-emitting diodes. <i>Journal of Applied Physics</i> , <b>2018</b> , 123, 104502	2.5	35
290	Degradation of (InAlGa) <sub>x</sub> N-based UV-B light emitting diodes stressed by current and temperature. <i>Journal of Applied Physics</i> , <b>2015</b> , 118, 094504	2.5	35
289	(Al,Ga) <sub>x</sub> N overgrowth over AlN ridges oriented in [1120] and [1100] direction. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2011</b> , 8, 2022-2024		34
288	Performance and degradation of continuous-wave InGa <sub>x</sub> N multiple-quantum-well laser diodes on epitaxially laterally overgrown GaN substrates. <i>Applied Physics Letters</i> , <b>2000</b> , 77, 1931-1933	3-4	34
287	Above band gap absorption spectra of the arsenic antisite defect in low temperature grown GaAs and AlGaAs. <i>Applied Physics Letters</i> , <b>1996</b> , 68, 37-39	3-4	34
286	MOVPE-grown AlGa <sub>x</sub> N-based tunnel heterojunctions enabling fully transparent UVC LEDs. <i>Photonics Research</i> , <b>2019</b> , 7, B7	6	34
285	Electronic properties of Si-doped Al <sub>x</sub> Ga <sub>1-x</sub> N with aluminum mole fractions above 80%. <i>Journal of Applied Physics</i> , <b>2016</b> , 120, 145702	2.5	34
284	Metamorphic Al <sub>0.5</sub> Ga <sub>0.5</sub> N:Si on AlN/sapphire for the growth of UVB LEDs. <i>Journal of Crystal Growth</i> , <b>2017</b> , 464, 185-189	1.6	33
283	Structural and optical properties of semipolar AlGa <sub>x</sub> N grown on sapphire by metalorganic vapor phase epitaxy. <i>Journal of Crystal Growth</i> , <b>2013</b> , 367, 42-47	1.6	33
282	Crystal orientation of GaN layers on (1010) m-plane sapphire. <i>Physica Status Solidi (B): Basic Research</i> , <b>2011</b> , 248, 583-587	1.3	33
281	Shock-induced band-gap shift in GaN: Anisotropy of the deformation potentials. <i>Physical Review B</i> , <b>2005</b> , 71,	3-3	33

280	Gas Sensing of Nitrogen Oxide Utilizing Spectrally Pure Deep UV LEDs. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2017</b> , 23, 29-36	3.8	32
279	Temperature and excitation power dependent photoluminescence intensity of GaInN quantum wells with varying charge carrier wave function overlap. <i>Journal of Applied Physics</i> , <b>2010</b> , 107, 033510	2.5	32
278	A-plane GaN epitaxial lateral overgrowth structures: Growth domains, morphological defects, and impurity incorporation directly imaged by cathodoluminescence microscopy. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 212111	3.4	32
277	Controlled coalescence of MOVPE grown AlN during lateral overgrowth. <i>Journal of Crystal Growth</i> , <b>2013</b> , 368, 83-86	1.6	31
276	Effect of temperature and strain on the optical polarization of (In)(Al)GaN ultraviolet light emitting diodes. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 261105	3.4	31
275	Controlling the morphology transition between step-flow growth and step-bunching growth. <i>Journal of Crystal Growth</i> , <b>2017</b> , 478, 187-192	1.6	30
274	Degradation of (In)AlGaIn-Based UVB LEDs and Migration of Hydrogen. <i>IEEE Photonics Technology Letters</i> , <b>2019</b> , 31, 529-532	2.2	29
273	Topography of (202 $\bar{1}$ ) AlGaIn, GaN and InGaIn layers grown by metal-organic vapor phase epitaxy. <i>Journal of Crystal Growth</i> , <b>2012</b> , 356, 70-74	1.6	29
272	High aluminium content and high growth rates of AlGaIn in a close-coupled showerhead MOVPE reactor. <i>Journal of Crystal Growth</i> , <b>2011</b> , 315, 229-232	1.6	29
271	Correlation of sapphire off-cut and reduction of defect density in MOVPE grown AlN. <i>Physica Status Solidi (B): Basic Research</i> , <b>2016</b> , 253, 809-813	1.3	29
270	Effect of heterostructure design on carrier injection and emission characteristics of 295 nm light emitting diodes. <i>Journal of Applied Physics</i> , <b>2015</b> , 117, 195704	2.5	28
269	Internal efficiency of InGaIn light-emitting diodes: Beyond a quasiequilibrium model. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 121105	3.4	28
268	Two-section InGaIn multiple-quantum-well laser diode with integrated electroabsorption modulator. <i>Applied Physics Letters</i> , <b>2002</b> , 80, 3283-3285	3.4	28
267	Dominance of radiative recombination from electron-beam-pumped deep-UV AlGaIn multi-quantum-well heterostructures. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 181105	3.4	28
266	Polarity determination of polar and semipolar (112 $\bar{2}$ ) InN and GaN layers by valence band photoemission spectroscopy. <i>Journal of Applied Physics</i> , <b>2013</b> , 114, 173503	2.5	27
265	Surface morphology of homoepitaxial GaN grown on non- and semipolar GaN substrates. <i>Physica Status Solidi (B): Basic Research</i> , <b>2011</b> , 248, 574-577	1.3	27
264	Current-induced degradation and lifetime prediction of 310 nm ultraviolet light-emitting diodes. <i>Photonics Research</i> , <b>2019</b> , 7, B36	6	27
263	Determination of lattice parameters, strain state and composition in semipolar III-nitrides using high resolution X-ray diffraction. <i>Journal of Applied Physics</i> , <b>2013</b> , 114, 213509	2.5	26

262	Uniformity of the wafer surface temperature during MOVPE growth of GaN-based laser diode structures on GaN and sapphire substrate. <i>Journal of Crystal Growth</i> , <b>2011</b> , 315, 5-9	1.6	26
261	Dry-etching and characterization of mirrors on III-nitride laser diodes from chemically assisted ion beam etching. <i>Journal of Crystal Growth</i> , <b>1998</b> , 189-190, 846-849	1.6	26
260	Improved performance of UVC-LEDs by combination of high-temperature annealing and epitaxially laterally overgrown AlN/sapphire. <i>Photonics Research</i> , <b>2020</b> , 8, 589	6	26
259	Influence of light absorption on the performance characteristics of UV LEDs with emission between 239 and 217 nm. <i>Applied Physics Express</i> , <b>2019</b> , 12, 012008	2.4	26
258	The effects of magnesium doping on the modal loss in AlGaIn-based deep UV lasers. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 081103	3.4	25
257	On the optical polarization properties of semipolar InGaIn quantum wells. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 051103	3.4	25
256	Recombination mechanisms and thermal droop in AlGaIn-based UV-B LEDs. <i>Photonics Research</i> , <b>2017</b> , 5, A44	6	24
255	Growth and characterizations of semipolar (112̄̄̄) InN. <i>Journal of Applied Physics</i> , <b>2012</b> , 112, 013530	2.5	24
254	DFB Laser Diodes Based on GaN Using 10th Order Laterally Coupled Surface Gratings. <i>IEEE Photonics Technology Letters</i> , <b>2018</b> , 30, 231-234	2.2	23
253	Impact of electron irradiation on electron holographic potentiometry. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 094102	3.4	23
252	Influence of quantum-well-barrier composition on gain and threshold current in AlGaIn lasers. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 101116	3.4	22
251	Optical light polarization and light extraction efficiency of AlGaIn-based LEDs emitting between 264 and 220 nm. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, SCCB20	1.4	21
250	AlGaIn layer structures for deep UV emitters on laterally overgrown AlN/sapphire templates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2013</b> , 210, 451-454	1.6	21
249	. <i>IEEE Photonics Technology Letters</i> , <b>1993</b> , 5, 1386-1388	2.2	21
248	Milliwatt power 233 nm AlGaIn-based deep UV-LEDs on sapphire substrates. <i>Applied Physics Letters</i> , <b>2020</b> , 117, 111102	3.4	21
247	Impact of inhomogeneous broadening on optical polarization of high-inclination semipolar and nonpolar InxGa1-xN/GaN quantum wells. <i>Physical Review B</i> , <b>2016</b> , 93,	3.3	20
246	Spatial clustering of defect luminescence centers in Si-doped low resistivity Al0.82Ga0.18N. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 072103	3.4	20
245	Laser Scribing for Facet Fabrication of InGaIn MQW Diode Lasers on Sapphire Substrates. <i>IEEE Photonics Technology Letters</i> , <b>2010</b> , 22, 416-418	2.2	20

244	Novel shadow mask molecular beam epitaxial regrowth technique for selective doping. <i>Applied Physics Letters</i> , <b>1993</b> , 62, 3180-3182	3.4	20
243	Investigation of inversion domain formation in AlN grown on sapphire by MOVPE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2012</b> , 9, 496-498		19
242	Single phase {112 $\bar{1}$ } GaN on (101 $\bar{0}$ ) sapphire grown by metal-organic vapor phase epitaxy. <i>Journal of Crystal Growth</i> , <b>2011</b> , 331, 25-28	1.6	19
241	Indium incorporation efficiency and critical layer thickness of (202 $\bar{1}$ ) InGaN layers on GaN. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 202102	3.4	19
240	(In)AlGa $\bar{N}$ deep ultraviolet light emitting diodes with optimized quantum well width. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2010</b> , 207, 2198-2200	1.6	19
239	Polarization dependence of the electroabsorption in low-temperature grown GaAs for above band-gap energies. <i>Applied Physics Letters</i> , <b>1996</b> , 68, 2968-2970	3.4	19
238	Displacement Talbot lithography for nano-engineering of III-nitride materials. <i>Microsystems and Nanoengineering</i> , <b>2019</b> , 5, 52	7.7	19
237	UV-C Lasing From AlGa $\bar{N}$ Multiple Quantum Wells on Different Types of AlN/Sapphire Templates. <i>IEEE Photonics Technology Letters</i> , <b>2015</b> , 27, 1969-1972	2.2	18
236	Status and Prospects of AlN Templates on Sapphire for Ultraviolet Light-Emitting Diodes. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2020</b> , 217, 1901022	1.6	18
235	Growth mode of InGa $\bar{N}$ on GaN (0001) in MOVPE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2009</b> , 6, S565-S569		18
234	Characteristics of InGa $\bar{N}$ -AlGa $\bar{N}$ multiple-quantum-well laser diodes. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>1998</b> , 4, 498-504	3.8	18
233	Analysis of wavelength-dependent performance variations of GaN-based ultraviolet lasers <b>2007</b> ,		18
232	Efficient carrier-injection and electron-confinement in UV-B light-emitting diodes. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2016</b> , 213, 210-214	1.6	18
231	V-pit to truncated pyramid transition in AlGa $\bar{N}$ -based heterostructures. <i>Semiconductor Science and Technology</i> , <b>2015</b> , 30, 114010	1.8	17
230	Polarization of eigenmodes in laser diode waveguides on semipolar and nonpolar GaN. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2010</b> , 4, 1-3	2.5	17
229	InGa $\bar{N}$ /Ga $\bar{N}$ Disk Laser for Blue-Violet Emission Wavelengths. <i>IEEE Photonics Technology Letters</i> , <b>2010</b> , 22, 652-654	2.2	16
228	Facet formation for laser diodes on nonpolar and semipolar GaN. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2010</b> , 207, 1361-1364	1.6	16
227	Near band edge and defect emissions from epitaxial lateral overgrown a-plane GaN with different stripe orientations. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 8-12	1.6	16



226	High contrast electro-optic n-i-p-i doping superlattice modulator. <i>Applied Physics Letters</i> , <b>1993</b> , 62, 1916-1918	3.4	16
225	Localization of current-induced degradation effects in (InAlGa)N-based UV-B LEDs. <i>Journal of Applied Physics</i> , <b>2018</b> , 124, 084504	2.5	16
224	MOVPE growth of semipolar (112̄2) Al <sub>1-x</sub> In <sub>x</sub> N across the alloy composition range (0.00-0.55). <i>Journal of Crystal Growth</i> , <b>2015</b> , 411, 106-109	1.6	15
223	Reliability of UVC LEDs fabricated on AlN/sapphire templates with different threading dislocation densities. <i>Applied Physics Letters</i> , <b>2020</b> , 117, 241104	3.4	15
222	Effect of Electron Blocking Layer Doping and Composition on the Performance of 310 nm Light Emitting Diodes. <i>Materials</i> , <b>2017</b> , 10,	3.5	15
221	Growth mode transition and relaxation of thin InGaN layers on GaN (0001). <i>Journal of Crystal Growth</i> , <b>2013</b> , 372, 65-72	1.6	15
220	Anisotropic strain on phonons in a-plane GaN layers studied by Raman scattering. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2008</b> , 19, 51-57	2.1	15
219	Ultraviolet InAlGaN multiple-quantum-well laser diodes. <i>Physica Status Solidi A</i> , <b>2003</b> , 200, 118-121		15
218	The Integration of In <sub>x</sub> Ga <sub>1-x</sub> N Multiple-Quantum-Well Laser Diodes with Copper Substrates by Laser Lift-Off. <i>Japanese Journal of Applied Physics</i> , <b>2000</b> , 39, L1203-L1205	1.4	15
217	Electrical properties and microstructure formation of V/Al-based n-contacts on high Al mole fraction n-AlGa <sub>1-x</sub> N layers. <i>Photonics Research</i> , <b>2020</b> , 8, 1381	6	15
216	Anisotropic optical properties of semipolar AlGa <sub>1-x</sub> N layers grown on m-plane sapphire. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 182102	3.4	14
215	Analysis of crystal orientation in AlN layers grown on m-plane sapphire. <i>Journal of Crystal Growth</i> , <b>2014</b> , 400, 54-60	1.6	14
214	Excitonic recombination in epitaxial lateral overgrown AlN on sapphire. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 212108	3.4	14
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212	Growth of semipolar (10̄5 bar 1 bar 3̄) InN on m -plane sapphire using MOVPE. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2010</b> , 4, 127-129	2.5	14
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